Product Bulletin

Document #:PB27653X
Issue Date: 04 Nov 2026

Title of Change:	Silicon buffer thickness and blank implant dose changes
Effective date:	04 Nov 2026
Contact information:	Contact your local onsemi Sales Office
Type of notification:	This Product Bulletin is for notification purposes only. onsemi will proceed with implementation of this change upon publication of this Product Bulletin.
Change Category:	Wafer Fab Change
Change Sub-Category(s):	Manufacturing Process Change

Sites Affected:

onsemi Sites	**External Foundry/Subcon Sites**
onsemi Bucheon, Korea	None

Description and Purpose:

onsemi would like to announce that Silicon thickness and Blank implant dose have been optimized for IGBT 650V families.

Item	Before Change	After change
Silicon buffer thickness	9um	12um
Blank implant dose	Phosphorus, 6.0E11 ions/cm2	Phosphorus, 6.2E11 ions/cm2

The datasheet specifications and product electrical performance remain unchanged.

This change does not impact to Form, Fit and Function of affected part.

List of Affected Standard Parts:

***Note**: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the **PCN Customized Portal**.*

FGH4L75T65MQDC50	FGHL75T65MQDTL4	FGHL75T65MQDT
FGHL75T65MQD	FGH4L50T65MQDC50	FGHL50T65MQDTL4
FGHL50T65MQDT	FGHL50T65MQD	FGHL40T65MQDT
FGHL40T65MQD		